

Ref #	Hits	Search Query	DBs	Default Operator	Plurals	Time Stamp
L1	818	organic adj ((thin adj film adj transistor\$1) TFT\$1)	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT ; IBM_TDB	OR	ON	2005/06/07 11:03
L2	12	L1 and ((gate near oxide near (layer film)) and (gate near (dielectric insulat\$3) near (layer film)) and (gate near electrode))	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT ; IBM_TDB	OR	ON	2005/06/07 11:24
L3	3	("5347144" "5946551" "5981970").PN.	US-PGPUB; USPAT; USOCR	OR	ON	2005/06/07 11:15
L4	6	("4724106" "5075738" "5206525" "5347144" "5625199" "5705826").PN.	US-PGPUB; USPAT; USOCR	OR	ON	2005/06/07 11:16
L5	2	("5347144" "5355235").PN.	US-PGPUB; USPAT; USOCR	OR	ON	2005/06/07 11:18
L6	2	("4873556" "5107308").PN.	US-PGPUB; USPAT; USOCR	OR	ON	2005/06/07 11:20
L7	22	L1 and (((gate near oxide) (Ta2O3 Al2O3)) and (gate near (dielectric insulat\$3) near (layer film)) and (gate near electrode))	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT ; IBM_TDB	OR	ON	2005/06/07 11:25
L8	3	("5347144" "5625199" "5981970").PN.	US-PGPUB; USPAT; USOCR	OR	ON	2005/06/07 11:33
S1	1601	257/40.ccls.	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT ; IBM_TDB	OR	ON	2005/06/06 16:31
S2	1362	S1 and organic	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT ; IBM_TDB	OR	ON	2005/06/06 16:53
S3	184	S2 and (gate near (oxide insulat\$3 dielectric) near (layer film))	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT ; IBM_TDB	OR	ON	2005/06/06 16:47

S4	13	S2 and (gate near oxide near (layer film))	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT ; IBM_TDB	OR	ON	2005/06/06 16:53
S5	388310	"257"/\$.ccls. "438"/\$.ccls.	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT ; IBM_TDB	OR	ON	2005/06/06 16:52
S6	44641	S5 and organic	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT ; IBM_TDB	OR	ON	2005/06/06 16:53
S7	27	S6 and ((gate near oxide near (layer film)) with (gate near (dielectric insulat\$3) near (layer film)) with (gate near electrode))	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT ; IBM_TDB	OR	ON	2005/06/06 16:59
S8	817	organic adj ((thin adj film adj transistor\$1) TFT\$1)	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT ; IBM_TDB	OR	ON	2005/06/06 16:59
S9	2	S8 and ((gate near oxide near (layer film)) with (gate near (dielectric insulat\$3) near (layer film)) with (gate near electrode))	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT ; IBM_TDB	OR	ON	2005/06/07 11:03